

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re Patent Application of

NAKAYAMA ET AL.

Atty. Ref.: 925-342

Serial No. 10/581,247

Group: 2811

Filed: May 31, 2006

Examiner: Unknown

For: SILICON CARBIDE SEMICONDUCTOR DEVICE AND  
MANUFACTURING METHOD THEREFOR

\* \* \* \* \*

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**INFORMATION DISCLOSURE STATEMENT**

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449.

- ☐ All listed documents are attached.
- ☒ Copies of U.S. Patent Publications are not required and are not attached.
- ☒ Listed foreign patent publications and other documents are enclosed.
- ☒ The EP 1215730 reference corresponds to the WO 01/018872 reference; U.S.

Patent 6,121,633 corresponds to the JP 2002-514355 reference; and U.S. Patent 5,958,132 corresponds to the JP 7-267795 reference..

☒ The listed documents were cited in the ISR and copies are submitted herewith for the Examiner's consideration in this US National Phase Application.

This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

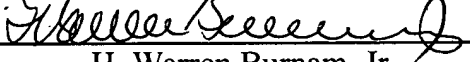
The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

NAKAYAMA ET AL.  
Serial No. 10/581,247

The Commissioner is authorized to charge the undersigned's deposit account #14-1140 in whatever amount is necessary for entry of these papers and the continued pendency of the captioned application.

Respectfully submitted,  
NIXON & VANDERHYE P.C.

January 8, 2007

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**INFORMATION DISCLOSURE  
CITATION**

ATTY. DOCKET NO.

SERIAL NO.

925-342

10/581,247

APPLICANT

NAKAYAMA ET AL.

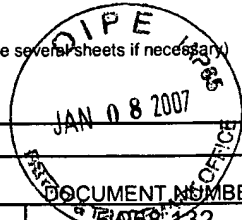
FILING DATE

GROUP

May 31, 2006

2811

(Use several sheets if necessary)


**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,958,132	9-1999	Takahashi et al.			
	6,121,633	9-2000	Singh et al.			

**FOREIGN PATENT DOCUMENTS**

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
					YES	NO
2001/018872 A1	3-2001	WO			X	
2000-001398 A	1-2000	JP			Partial	
03-171772 A	7-1999	JP			Partial	
2002-514355 A	5-2002	JP			Partial	
11-060390 A	3-1999	JP			Partial	
7-267795 A	10-1995	JP			Partial	
1 215 730 A1	6-2002	EP				

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

	Translation of the International Preliminary Report on Patentability mailed August 3, 2006 in corresponding PCT application no. PCT/JP2004/017888
	Matsunami, "Semiconductor SiC Technology and Applications", Nikkan Kogyo Shimbunsha, pp. 218-221
	Agarwal et al, "Dynamic Performance of 3.1 kV 4H-SiC Asymmetrical GTO Thyristors", Materials Science Forum Vols. 389-393, (2002), pp. 1349-1352
	Lendenmann et al, "High-Power SiC Diodes: Characteristics, Reliability and Relation to Material Defects", Materials Science Forum Vols. 389-393, (2002), pp. 1259-1264
	Matsunami et al., "Step-Controlled Epitaxial Growth of SiC: High Quality Homoepitaxy", Materials Science and Engineering, R20, Reports: A Review Journal, (1997), pp. 125-166

\*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)